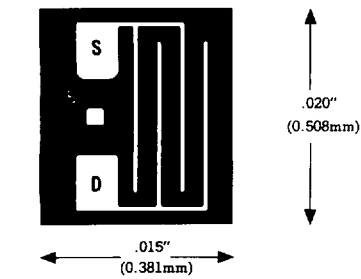


PRODUCT CATALOG

N-CHANNEL JUNCTION FET

CHIP NUMBER

FN39.8



Die Size: 15 x 20 (mils)
0.381 x 0.508(mm)
3.5 x 4.5 (mils)
0.089 x 0.114(mm)
Pad Size: 0.089 x 0.114(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

- It is advisable that:
- a) the die be eutectically mounted with gold silicon preform 98/2%.
 - b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	-40	-50	-70	V	VDS = 0, IG = 1μA
IDSS	0.1	3.0	10	mA	VDS = 20V, VGS = 0
gfs	0.5	1.8	3.5	μmho	VDS = 20V, VGS, = 0
IGSS		-10	-100	pA	VGS = -30V, VDS = 0
rDS		500	2000	Ω	VDS = 100mV, VGS = 0
VGS(off)		-2.5	-6.0	V	VDS = 20V, ID = 1mA
Crss		2.0	4.0	pF	VDS = 20V, VGS = 0, f = 1MHz
Ciss		5.0	7.0	pF	VDS = 20V, VGS = 0, f = 1MHz
ēn		10	30	nV/√Hz	VDS = 15V, ID = .2mA, f = 10Hz

TYPICAL DEVICE TYPES: SDF500 Thru SDF 505, 2N5515 - 2N5524, 2N4867, 2N4868

CHIP TYPE FN39.8

